

HIGH POWER RECTIFIER DIODES

- **Junction Size:** Square 210 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 600 and 1200 V
- **Passivation Process:** Glassivated MESA
- **Reference IR Packaged Part:** 40HF Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1000mV	T _J = 25°C I _F = 25A
V _{RRM} Reverse Breakdown Voltage Range	600 and 1200V	T _J = 25°C I _R = 100μA (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
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Chip Dimensions	210 x 210 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 μm
Maximum Width of Sawing Line	130 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR210DG..HCB Series

Bulletin I0133J 05/99

Ordering Information Table

Device Code						
IR	210	D	G	12	H	CB
①	②	③	④	⑤	⑥	⑦

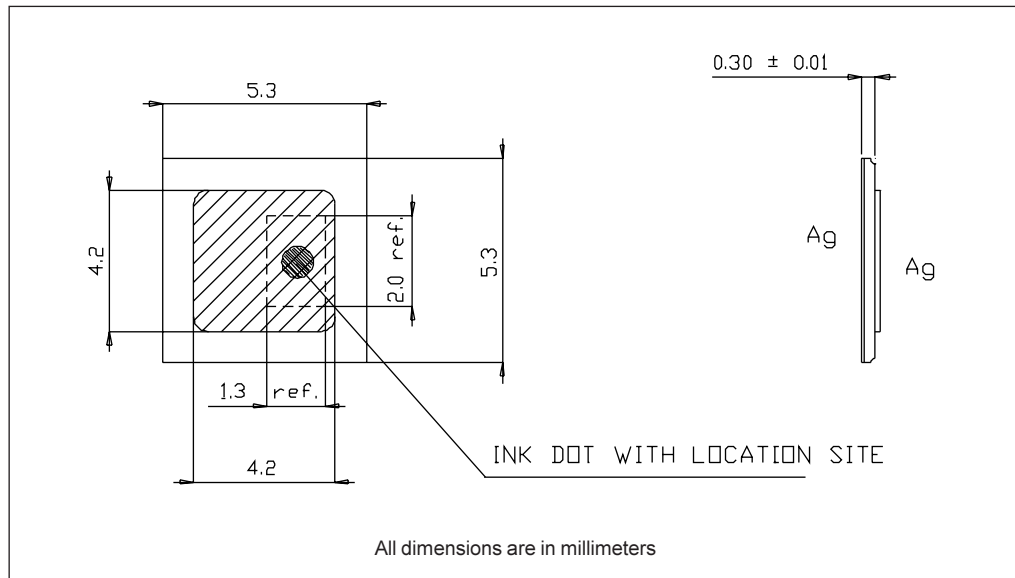
- 1** - International Rectifier Device
- 2** - Chip Dimension in Mils
- 3** - Type of Device: D = Standard Recovery Diode
- 4** - Passivation Process: G = Glassivated MESA
- 5** - Voltage code: Code x 100 = V_{RRM}
- 6** - Metallization: H = Silver (Anode) - Silver (Cathode)
- 7** - Probed Uncut Die

Available Class

06 = 600V

12 = 1200V

Outline Table



Wafer Layout

